



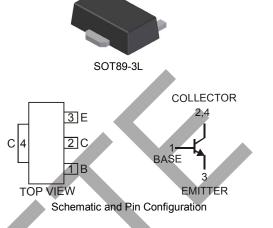
#### NPN SURFACE MOUNT TRANSISTOR

#### Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DCX69)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

## Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)



#### **Maximum Ratings** $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	25	V
Collector-Emitter Voltage	V <sub>CEO</sub>	20	V
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	V
Collector Current	lc	1.0	A
Peak Pulse Current	Ісм	2.0	А

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T <sub>A</sub> = 25°C	PD	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @T <sub>A</sub> = 25°C	R <sub>θJA</sub>	125	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteris	tic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4	)						
Collector-Base Breakdown Voltage		V <sub>(BR)CBO</sub>	25	_	—	V	$I_{\rm C} = 100 \mu A$ , $I_{\rm E} = 0$
Collector-Emitter Breakdown Voltag	ge	V <sub>(BR)CEO</sub>	20	_		V	$I_{\rm C}$ = 10mA, $I_{\rm B}$ = 0
Emitter-Base Breakdown Voltage		V <sub>(BR)EBO</sub>	5.0	_	—	V	$I_{\rm E} = 100 \mu A, I_{\rm C} = 0$
Collector-Base Cutoff Current		I <sub>CBO</sub>	_	_	0.1 10	μA	V <sub>CB</sub> = 25V, I <sub>E</sub> = 0
							V <sub>CB</sub> = 25V, I <sub>E</sub> = 0, T <sub>A</sub> = 150°C
Emitter-Base Cutoff Current		I <sub>EBO</sub>	—		10	μA	$V_{EB} = 5.0V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)							
	DCX68, DCX68-25	h <sub>FE</sub>	50			-	V <sub>CE</sub> = 10V, I <sub>C</sub> = 5.0mA
DC Current Gain	DCX00, DCX00-23		60		_		V <sub>CE</sub> = 1.0V, I <sub>C</sub> = 1.0A
	DCX68		85		375		V <sub>CE</sub> = 1.0V, I <sub>C</sub> = 500mA
	DCX68-25		160		375		V <sub>CE</sub> = 1.0V, I <sub>C</sub> = 500mA
Collector-Emitter Saturation Voltage	e	V <sub>CE(SAT)</sub>	_	_	0.5	V	I <sub>C</sub> = 1.0A, I <sub>B</sub> = 100mA
Base-Emitter Turn-On Voltage		V <sub>BE(ON)</sub>	_	_	1.0	V	I <sub>C</sub> = 1.0A, V <sub>CE</sub> = 1.0V
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product		f <sub>T</sub>	_	330		MHz	V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 100mA, f = 100MHz
Output Capacitance		C <sub>obo</sub>	_		25	pF	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz

1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

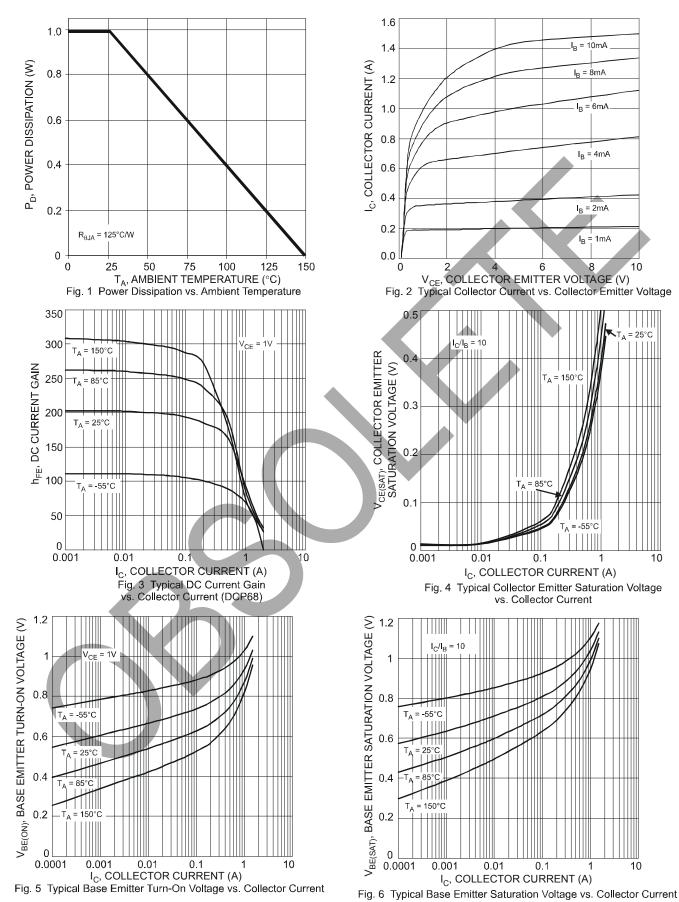
3. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can

be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

4. Measured under pulsed conditions. Pulse width = 300 $\mu$ s. Duty cycle  $\leq$ 2%.

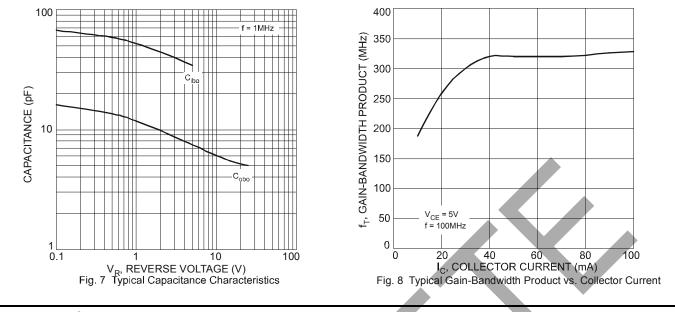
Notes:







## DCX68/-25

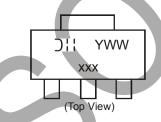


#### Ordering Information (Note 5)

Device	Packaging	Shipping
DCX68-13	SOT89-3L	2500/Tape & Reel
DCX68-25-13	SOT89-3L	2500/Tape & Reel

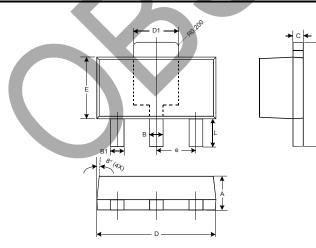
Notes: 5. For packaging details, go to our website at http://www.diodes.com/ap02007.pdf.

# **Marking Information**



xxx = Product Type Marking Code: N12 = DCX68 N12-25 = DCX68-25 YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

## **Package Outline Dimensions**

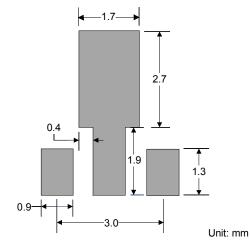


SOT89-3L					
Dim	Min	Мах	Тур		
Α	1.40	1.60	1.50		
в	0.45	0.55	0.50		
B1	0.37	0.47	0.42		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.50	1.70	1.60		
Е	2.40	2.60	2.50		
е			1.50		
Н	3.95	4.25	4.10		
L	0.90	1.20	1.05		
All [	All Dimensions in mm				



DCX68/-25

# Suggested Pad Layout





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